

SST5114 P-CHANNEL JFET



Linear Systems replaces discontinued Siliconix SST5114

This analog switch is designed for inverting switching into inverting input of an Operational Amplifier.

The SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

(See Packaging Information).

SST5114 Benefits:

- Low On Resistance
- $I_{D(off)} \le 500 \text{ pA}$
- Switches directly from TTL logic

SST5114 Applications:

- **Analog Switches**
- Commutators
- Choppers

FEATURES					
DIRECT REPLACEMENT FOR SILICONIX SST5114					
LOW ON RESISTANCE	$r_{DS(on)} \le 75\Omega$				
LOW CAPACITANCE	6pF				
ABSOLUTE MAXIMUM RATINGS @ 25°C (unless otherwise noted)					
Maximum Temperatures					
Storage Temperature	-55°C to +200°C				
Operating Junction Temperature	-55°C to +200°C				
Maximum Power Dissipation					
Continuous Power Dissipation	500mW				
MAXIMUM CURRENT					
Gate Current (Note 1)	I _G = -50mA				
MAXIMUM VOLTAGES					
Gate to Drain Voltage	V _{GDS} = 30V				
Gate to Source Voltage	V _{GSS} = 30V				

SST5114 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

3313114 ELECTRICAL CHARACTERISTICS @ 25 C (utiless ottlerwise floted)						
SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
BV _{GSS}	Gate to Source Breakdown Voltage	30				$I_{G} = 1\mu A$, $V_{DS} = 0V$
$V_{GS(off)}$	Gate to Source Cutoff Voltage	4		10		$V_{DS} = -15V, I_{D} = -1nA$
V _{GS(F)}	Gate to Source Forward Voltage		-0.7	-1	V	$I_G = -1 \text{mA}, V_{DS} = 0 \text{V}$
			-1.0	-1.3		$V_{GS} = 0V, I_D = -15mA$
$V_{DS(on)}$	Drain to Source On Voltage		-0.7			$V_{GS} = 0V$, $I_D = -7mA$
			-0.5			$V_{GS} = 0V$, $I_D = -3mA$
I _{DSS}	Drain to Source Saturation Current (Note 2)	-30		-90	mA	$V_{DS} = -18V, V_{GS} = 0V$
I _{GSS}	Gate Reverse Current		5	500		$V_{GS} = 20V, \ V_{DS} = 0V$
I _G	Gate Operating Current		-5			$V_{DS} = -15V, I_{D} = -1mA$
	Drain Cutoff Current		-10	-500	рA	$V_{DS} = -15V, V_{GS} = 12V$
I _{D(off)}			-10			V _{DS} = -15V, V _{GS} = 7V
			-10			$V_{DS} = -15V, V_{GS} = 5V$
r _{DS(on)}	Drain to Source On Resistance			75	Ω	$I_{D} = -1 \text{mA}, V_{GS} = 0 \text{V}$

SST5114 DYNAMIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS
g fs	Forward Transconductance		4.5		mS	$V_{DS} = -15V, I_{D} = 1mA, f = 1kHz$
g os	Output Conductance		20		μS	
r _{DS(on)}	Drain to Source On Resistance			75	Ω	$I_D = 0A$, $V_{GS} = 0V$, $f = 1kHz$
C _{iss}	Input Capacitance		20	25		$V_{DS} = -15V$, $V_{GS} = 0V$, $f = 1MHz$
			5	7	pF	$V_{DS} = 0V$, $V_{GS} = 12V$, $f = 1MHz$
C_{rss}	Reverse Transfer Capacitance		6			$V_{DS} = 0V$, $V_{GS} = 7V$, $f = 1MHz$
			6			$V_{DS} = 0V$, $V_{GS} = 5V$, $f = 1MHz$
e _n	Equivalent Noise Voltage		20		nV/√Hz	$V_{DG} = 10V, I_D = 10mA, f = 1kHz$

SST5114 SWITCHING CHARACTERISTICS @ 25°C (unless otherwise noted)

	SYMBOL	CHARACTERISTIC		UNITS	CONDITIONS	
	t _{d(on)}	Turn On Time	6		$V_{GS}(L) = -11V$	
ĺ	t _r	Turn On Rise Time	10	ns	$V_{GS}(H) = 0V$	
ĺ	t _{d(off)}	Turn Off Time	6		113	See Switching Circuit
ĺ	t _f	Turn Off Fall Time	15		Ü	

Note 1 - Absolute maximum ratings are limiting values above which SST5114 serviceability may be impaired. Note 2 - Pulse test: PW≤ 300 µs, Duty Cycle ≤ 3%

SST5114 SWITCHING CIRCUIT PARAMETERS

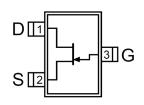
V _{DD}	-10V
V_{GG}	20V
R_L	430Ω
R_G	100Ω
I _{D(on)}	-15mA

Micross Components Europe

Available Packages:

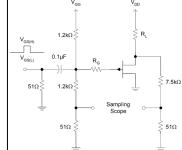
SST5114 in SOT-23 SST5114 in bare die.

Please contact Micross for full package and die dimensions



SOT-23 (Top View)





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